

PATENT
006775USA
7828.7082

Application No. 10/632,882

IN THE SPECIFICATION:

Please replace paragraph 0022 with the following amended paragraph:

[0022] A copper seed layer deposited over the barrier layer 124 is typically used as the electroplating electrode. However, a continuous, smooth, and uniform film is preferred. Otherwise, the electroplating current will be directed only to the areas covered with copper or be preferentially directed to areas covered with thicker copper. Depositing the copper seed layer presents its own difficulties. An IMP deposited seed layer provides good bottom coverage in high aspect-ratio holes, but its sidewall coverage can be small such that that the resulting thin films can be rough or discontinuous. A thin CVD seed layer can also be too rough. A thicker CVD seed layer, or CVD copper over IMP copper, may require an excessively thick seed layer to achieve the required continuity.